

OCT 25 2004

SHEET 1 OF 23

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 248402US99D	SERIAL NO. 10/767,994		
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT		Jamal RAMDANI, et al.			
		FILING DATE		GROUP			
		February 2, 2004		2815			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AA		3,802,957	04/09/74	Ladany et al.			
AB		4,174,422	11/13/79	Matthews et al.			
AC		4,404,265	09/13/83	Manasevit			
AD		4,482,906	11/13/84	Hovel et al.			
AE		4,523,211	06/11/85	Morimoto et al.			
AF		4,661,176	04/28/87	Manasevit			
AG		4,793,872	12/27/88	Meunier et al.			
AH		4,846,926	07/11/89	Kay et al.			
AJ		4,855,249	08/08/89	Akasaki et al.			
AI		4,891,091	01/02/90	Shastry			
AK		4,912,087	03/27/90	Aslam et al.			
AL		4,928,154	05/22/90	Umeno et al.			
AM		4,963,949	10/16/90	Wanlass et al.			
AN		5,141,894	08/25/92	Bisaro et al.			
AO		5,159,413	10/27/92	Calviello et al.			
AP		5,173,474	12/22/92	Connell et al.			
AQ		5,221,367	06/22/93	Chisholm et al.			
AR		5,225,031	07/06/93	McKee et al.			
AS		5,358,925	10/25/94	Neville Connell et al.			
AT		5,393,352	02/28/95	Summerfelt			
AU		5,418,216	05/23/95	Fork			
AV		5,450,812	09/19/95	McKee et al.			
AW		5,478,653	12/26/95	Guenzer			
AX		5,482,003	01/09/96	McKee et al.			
AY		5,514,484	05/07/96	Nashimoto			
AZ		5,556,463	09/17/96	Guenzer			
BA		5,588,995	12/31/96	Sheldon			
BB		5,670,798	09/23/97	Schetzina			
BC		5,733,641	03/31/98	Fork et al.			
BD		5,735,949	04/07/98	Manti et al.			
BE		5,741,724	04/21/98	Ramdani et al.			
BF		5,810,923	09/22/98	Yano et al.			
BG		5,830,270	11/03/98	McKee et al.			
BH		5,912,068	06/15/99	Jia			
BI		6,020,222	02/01/00	Wollesen			
BJ		6,045,626	04/04/00	Yano et al.			
BK		6,064,078	05/16/00	Northrup et al.			
BL		6,064,092	05/16/00	Park			
BM		6,096,584	08/01/00	Ellis-Monaghan et al.			
BN		6,103,008	08/15/00	McKee et al.			
BO		6,136,666	10/24/00	So			
BP		6,174,755	01/16/01	Manning			
BQ		6,180,486	01/30/01	Leobandung et al.			

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		APPLICANT Jamal RAMDANI, et al.				
		FILING DATE February 2, 2004		GROUP 2815		
		U.S. PATENT DOCUMENTS				
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS SUB CLASS	FILING DATE IF APPROPRIATE
	CA	3,766,370	10/16/73	Walther		
	CB	4,006,989	02/08/77	Andringa		
	CC	4,284,329	08/18/81	Smith et al.		
	CD	4,777,613	10/11/98	Shahan et al.		
	CE	4,802,182	01/31/89	Thornton et al.		
	CF	4,882,300	11/21/89	Inoue et al.		
	CG	4,896,194	01/23/90	Suzuki		
	CH	4,999,842	03/12/91	Huang et al.		
	CI	5,081,062	01/14/92	Vasudev et al.		
	CJ	5,155,658	10/13/92	Inam et al.		
	CK	5,248,564	09/28/93	Ramesh		
	CL	5,260,394	11/09/93	Tazaki et al.		
	CM	5,270,298	12/14/93	Ramesh		
	CN	5,286,985	02/15/94	Taddiken		
	CO	5,310,707	05/10/94	Oishi et al.		
	CP	5,326,721	07/05/94	Summerfelt		
	CQ	5,404,581	04/04/95	Honjo		
	CR	5,418,389	05/23/95	Watanabe		
	CS	5,436,759	07/25/95	Dijali et al.		
	CT	5,576,879	11/19/96	Nashimoto		
	CU	5,606,184	02/25/97	Abrokwah, et al.		
	CV	5,640,267	06/17/97	May et al.		
	CW	5,674,366	10/07/97	Hayashi et al.		
	CX	5,729,641	03/17/98	Chandonnet et al.		
	CY	5,790,583	08/04/98	Ho		
	CZ	5,825,799	10/20/98	Ho et al.		
	DA	5,857,049	01/05/99	Beranek et al.		
	DB	5,874,860	02/23/99	Brunel et al.		
	DC	5,926,496	07/20/99	Ho et al.		
	DD	5,937,285	08/10/99	Abrokwah, et al.		
	DE	5,981,400	11/09/99	Lo		
	DF	5,990,495	11/23/99	Ohba		
	DG	6,002,375	12/14/99	Corman et al.		
	DH	6,008,762	12/28/99	Nghiem		
	DI	6,055,179	04/25/00	Koganei et al.		
	DJ	6,107,653	08/22/00	Fitzgerald		
	DK	6,113,690	09/05/00	Yu et al.		
	DL	6,114,996	09/05/00	Nghiem		
	DM	6,121,642	09/19/00	Newns		
	DN	6,128,178	10/03/00	Newns		
	DO	6,143,072	11/07/00	McKee et al.		
	DP	6,184,144	02/06/01	Lo		
	DQ	6,222,654	04/24/01	Frigo		

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LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Jamal RAMDANI, et al.				
		FILING DATE February 2, 2004	GROUP 2815			
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
EWB	EA 4,484,332	11/20/84	Hawrylo			
	EB 4,815,084	03/21/89	Scifres et al.			
	EC 4,876,219	10/24/89	Eshita et al.			
	ED 4,963,508	10/16/90	Umeno et al.			
	EE 5,060,031	10/22/91	Abrokwah, et al.			
	EF 5,063,166	11/05/91	Mooney et al.			
	EG 5,116,461	05/26/92	Lebby et al.			
	EH 5,127,067	06/30/92	Delcoco et al.			
	EI 5,144,409	09/01/92	Ma			
	EJ 5,293,050	03/08/94	Chapple-Sokol et al.			
	EK 5,356,831	10/18/94	Calviello et al.			
	EL 5,391,515	02/21/95	Kao et al.			
	EM 5,442,191	08/15/95	Ma			
	EN 5,444,016	08/22/95	Abrokwah, et al.			
	EO 5,480,829	01/02/96	Abrokwah, et al.			
	EP 5,528,414	06/18/96	Oakley			
	EQ 5,614,739	03/25/97	Abrokwah et al.			
	ER 5,729,394	03/17/98	Sevier et al.			
	ES 5,731,220	03/24/98	Tsu et al.			
	ET 5,764,676	06/09/98	Paoli et al.			
	EU 5,777,762	07/07/98	Yamamoto			
	EV 5,778,018	07/07/98	Yoshikawa et al.			
	EW 5,778,116	07/07/98	Tomich			
	EX 5,801,105	09/01/98	Yano et al.			
	EY 5,828,080	10/27/98	Yano et al.			
	EZ 5,858,814	01/12/99	Goossen et al.			
	FA 5,861,966	01/19/99	Ortel			
	FB 5,883,996	03/16/99	Knapp et al.			
	FC 5,995,359	11/30/99	Klee et al.			
	FD 6,058,131	05/02/00	Pan			
	FE 6,137,603	10/24/00	Henmi			
	FF 6,146,906	11/14/00	Inoue et al.			
	FG 6,173,474	01/16/01	Conrad			
	FH 6,180,252	01/30/01	Farrell et al.			
	FI 4,242,595	12/30/0	Lehovec			
	FJ 4,398,342	08/16/83	Pitt et al.			
	FK 4,424,589	01/03/84	Thomas et al.			
	FL 4,876,208	10/24/89	Gustafson et al.			
	FM 4,482,422	11/84	McGinn et al.			
	FN 4,667,088	05/19/87	Kramer			
	FO 4,772,929	09/20/88	Manchester et al.			
	FP 4,841,775	06/27/89	Ikeda et al.			
	FQ 4,845,044	07/04/89	Ariyoshi et al.			

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			APPLICANT		Jamal RAMDANI, et al.		
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			February 2, 2004		2815		
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
GA	4,868,376	09/19/89	Lessin et al.				
GB	4,885,376	12/05/89	Verkade				
GC	4,888,202	12/89	Murakami et al.				
GD	4,891,091	12/90	Wanlass et al.				
GE	5,051,790	09/24/91	Hammer				
GF	5,055,445	10/08/91	Belt et al.				
GG	5,081,519	11/14/92	Nishimura et al.				
GH	5,143,854	09/01/92	Pirrung et al.				
GI	5,185,589	02/09/93	Krishnaswamy et al.				
GJ	5,191,625	03/02/93	Gustavsson				
GK	5,194,397	03/16/93	Cook et al.				
GL	5,208,182	05/04/93	Narayan et al.				
GM	5,216,729	06/01/93	Berger et al.				
GN	5,314,547	05/24/94	Heremans et al.				
GO	5,352,926	10/04/94	Andrews				
GP	5,356,509	10/18/94	Terranova et al.				
GQ	5,371,734	12/06/94	Fischer				
GR	5,372,992	12/94	Itozaki et al.				
GS	5,405,802	04/11/95	Yamagata et al.				
GT	5,442,561	08/15/95	Yoshizawa et al.				
GU	5,453,727	09/26/95	Shibasaki et al.				
GV	5,466,631	11/14/95	Ichikawa et al.				
GW	5,473,047	12/05/95	Shi				
GX	5,473,171	12/95	Summerfelt				
GY	5,479,033	12/26/95	Baca et al.				
GZ	5,486,406	01/23/96	Shi				
HA	5,491,461	02/13/96	Partin et al.				
HB	5,492,859	02/20/96	Sakaguchi et al.				
HC	5,494,711	02/27/96	Takeda et al.				
HD	5,504,035	04/02/96	Rostoker et al.				
HE	5,504,183	04/02/96	Shi				
HF	5,511,238	04/23/96	Bayraktaroglu				
HG	5,512,773	04/96	Wolf et al.				
HH	5,515,047	05/07/96	Yamakido et al.				
HI	5,515,810	05/14/96	Yamashita et al.				
HJ	5,519,235	05/96	Ramesh				
HK	5,549,977	08/96	Jin et al.				
HL	5,551,238	09/03/96	Pruett				
HM	5,552,547	09/03/96	Shi				
HN	5,589,284	12/31/96	Summerfelt et al.				
HO	5,602,418	02/11/97	Imai et al.				
HP	5,633,724	05/27/97	King et al.				

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			FILING DATE February 2, 2004	GROUP 2815		
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BBW	5,650,646	07/22/97	Summerfelt			
	5,656,382	08/12/97	Nashimoto			
	5,659,180	08/19/97	Shen et al.			
	5,661,112	08/26/97	Hatta et al.			
	5,679,965	11/95	Schetzina			
	5,725,641	03/10/98	MacLeod			
	5,745,631	04/28/98	Reinker			
	5,776,621	07/07/98	Nashimoto			
	5,777,350	07/07/98	Nakamura et al.			
	5,789,845	08/04/98	Wadaka et al.			
	5,792,569	08/11/98	Sun et al.			
	5,792,679	08/11/98	Nakato			
	5,796,648	08/18/98	Kawakubo et al.			
	5,801,072	09/01/98	Barber			
	5,812,272	09/22/98	King et al.			
	5,814,583	09/98	Itozaki et al.			
	5,825,055	10/20/98	Summerfelt			
	5,827,755	10/27/98	Yonchara et al.			
	5,833,603	11/10/98	Kovacs et al.			
	5,838,035	11/17/98	Ramesh			
	5,844,260	12/01/98	Ohori			
	5,846,846	12/08/98	Suh et al.			
	5,863,326	01/26/99	Nause et al.			
	5,872,493	02/16/99	Ella			
	5,879,956	03/99	Seon et al.			
	5,880,452	03/09/99	Plesko			
	5,883,564	03/16/99	Partin			
	5,907,792	05/25/99	Droopad et al.			
	5,937,274	08/10/99	Kondow et al.			
	5,948,161	09/07/99	Kizuki			
	5,959,879	09/28/99	Koo			
	5,966,323	10/99	Chen et al.			
	5,987,011	11/16/99	Toh			
	6,022,140	02/08/00	Fraden et al.			
	6,022,410	02/08/00	Yu et al.			
	6,023,082	02/08/00	McKee et al.			
	6,028,853	02/22/00	Haartsen			
	6,049,702	04/11/00	Tham et al.			
	6,078,717	06/20/00	Nashimoto et al			
	6,088,216	07/00	Laibowitz et al.			
	6,090,659	07/00	Laibowitz et al.			
	6,107,721	08/22/00	Lakin			
	6,153,010	11/28/00	Yokou et al			

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LIST OF REFERENCES CITED BY APPLICANT		APPLICANT		Jamal RAMDANI, et al.			
		FILING DATE	February 2, 2004			GROUP	2815
U.S. PATENT DOCUMENTS							
EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BHM	KA	6,153,454	11/28/00	Krivokapic			
	KB	6,191,011	02/01	Gilboa et al			
	KC	6,204,737	03/20/01	Ella			
	KD	6,224,669	05/01/01	Yi et al.			
	KE	6,225,051	05/01/01	Sugiyama et al.			
	KF	6,241,821	06/05/01	Yu et al.			
	KG	6,265,749	07/24/01	Gardner et al.			
	KH	6,313,486	11/01	Kencke et al.			
	KI	6,316,832	11/13/01	Tsuzuki et al.			
	KJ	2002/0008234	01/02	Emrick			
	KK	3,670,213	06/13/72	Nakawaga et al.			
	KL	4,756,007	07/05/88	Qureshi et al.			
	KM	4,773,063	09/20/88	Hunsperger et al.			
	KN	5,394,489	02/28/95	Koch			
	KO	5,406,202	04/11/95	Mehrgardt et al.			
	KP	5,528,067	06/18/96	Farb et al.			
	KQ	5,572,052	11/05/96	Kashihara et al.			
	KR	5,767,543	06/16/98	Ooms et al.			
	KS	6,175,497	01/16/01	Tseng et al.			
	KT	6,197,503	03/06/01	Vo-Dinh et al.			
	KU	6,248,459	06/19/01	Wang et al.			
	KV	6,252,261	06/26/01	Usui et al.			
	KW	6,255,198	07/03/01	Linthicum et al.			
	KX	6,268,269	07/31/01	Lee et al.			
	KY	6,291,319	09/18/01	Yu et al.			
	KZ	6,316,785	11/13/01	Nunoue et al.			
	LA	6,343,171	01/29/02	Yoshimura et al.			
	LB	4,965,649	10/23/90	Zanio et al.			
	LC	6,253,649	05/01	Kawahara et al.			
	LD	6,211,096	04/01	Allman et al.			
	LE	6,239,449	05/29/01	Fafard et al.			
	LF	2001/0013313	08/16/01	Droopad et al.			
	LG	6,184,044	02/06/01	Sone et al.			
	LH	6,011,646	01/04/00	Mirkarimi et al.			
	LI	5,227,196	07/13/93	Itoh			
	LJ	6,150,239	11/21/00	Goesele et al.			
	LK	5,441,577	08/15/95	Sasaki et al.			
	LL	4,459,325	07/10/84	Nozawa et al.			
	LM	4,392,297	07/12/83	Little			
	LN	4,289,920	09/15/81	Hovel			
	LO	5,281,834	01/25/94	Cambou et al.			
	LP	4,901,133	02/13/90	Curran et al.			
	LQ	5,514,904	06/07/96	Onga et al.			

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			APPLICANT Jamal RAMDANI, et al.		FILING DATE February 2, 2004		
LIST OF REFERENCES CITED BY APPLICANT			FILING DATE February 2, 2004		GROUP 2815		
			U.S. PATENT DOCUMENTS				
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MM	MA	5,553,089	09/03/96	Seki et al.			
	MB	5,528,057	06/18/96	Yanagase et al.			
	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
	MT	6,093,302	07/25/00	Montgomery			
	MU	6,372,813	04/16/02	Johnson et al.			
	MV	5,608,046	03/04/97	Cook et al.			
	MW	5,955,591	09/21/99	Imbach et al.			
	MX	6,022,963	02/08/00	McGall et al.			
	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
	NA	5,479,317	12/26/95	Ramesh			
	NB	5,306,649	04/26/94	Hebert			
	NC	5,962,069	10/05/99	Schindler et al.			
	ND	5,541,422	07/30/96	Wolf et al.			
	NE	5,873,977	02/23/99	Desu et al.			
	NF	5,538,941	07/23/96	Findikoglu et al.			
	NG	6,046,464	04/04/00	Schetzina			
	NH	6,235,145	05/22/01	Li et al.			
	NI	5,610,744	03/11/97	Ho et al.			
	NJ	5,280,013	01/18/94	Newman et al.			
	NK	6,348,373 B1	02/19/02	Ma et al.			
	NL	6,339,664 B1	01/15/02	Farjady et al.			
	NM	4,439,014	03/27/84	Stacy et al.			
	NN	4,889,402	12/26/89	Reinhart			
	NO	5,963,291	10/05/99	Wu et al.			
	NP	6,011,641	01/04/00	Shin et al.			
	NQ	6,340,788 B1	01/22/02	King et al.			

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BWB	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thomton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazelrigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
	OU	5,789,733	08/04/98	Jachimowicz et al.			
	OV	5,753,300	05/19/98	Wessels et al.			
	OW	6,208,453	03/27/01	Wessels et al.			
	OX	5,886,867	03/23/99	Chivukula et al.			
	OY	5,028,976	07/02/91	Ozaki et al.			
	OZ	5,869,845	02/09/99	Vander Wagt et al.			
	PA	5,596,214	01/21/97	Endo			
	PB	6,391,674 B2	05/21/02	Ziegler			
	PC	6,275,122 B1	08/14/01	Speidell et al.			
	PD	6,238,946 B1	05/29/01	Ziegler			
	PE	6,210,988 B1	04/03/01	Howe et al.			
	PF	6,392,257	05/21/02	Ramdani et al.			
	PG	4,442,590	04/17/84	Stockton et al.			
	PH	5,603,764	02/18/97	Matsuda et al.			
	PI	6,087,681	06/11/00	Shakuda			
	PJ	5,132,648	07/21/92	Trinh et al.			
	PK	6,427,066	07/30/02	Grube			
	PL	2002/0072245	06/13/02	Ooms et al.			
	PM	6,278,138 B1	08/21/01	Suzuki			
	PN	5,888,296	03/30/99	Ooms et al.			
	PO	5,198,269	03/30/93	Swartz et al.			
	PP	2002/0030246	03/14/02	Eisenbeiser et al.			
	PQ	2002/007143	04/25/02	Ramdani et al.			

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hB	QA	5,776,359	07/07/98	Schultz et al.			
	QB	5,569,953	10/29/96	Kikkawa et al.			
	QC	5,834,362	11/10/98	Miyagaki et al.			
	QD	6,248,621 B1	06/19/01	Wilk et al.			
	QE	5,266,355	11/30/93	Wernberg et al.			
	QF	6,277,436 B1	08/21/01	Stauf et al.			
	QG	6,039,803	03/21/00	Fitzgerald et al.			
	QH	5,619,051	04/08/97	Endo			
	QI	5,420,102	05/30/95	Harshavardhan et al.			
	QJ	5,210,763	05/11/93	Lewis et al.			
	QK	5,103,494	04/07/92	Mozer			
	QL	4,594,000	06/10/86	Falk et al.			
	QM	4,297,656	10/27/81	Pan			
	QN	5,244,818	09/14/93	Jokers et al.			
	QO	6,048,751	04/11/00	D'Asaro et al.			
	QP	5,484,664	01/16/96	Kitahara et al.			
	QQ	5,780,311	07/14/98	Beasom et al.			
	QR	6,438,281 B1	08/20/02	Tsukamoto et al.			
	QS	5,399,898	03/21/95	Rostoker			
	QT	6,271,619	08/07/01	Yamada et al.			
	QU	5,334,556	08/02/94	Guldi			
	QV	4,910,164	03/20/90	Shichijo			
	QW	4,952,420	08/28/90	Walters			
	QX	6,121,647	09/19/00	Yano et al.			
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	RJ	5,753,928	05/19/98	Krause			
	RK	5,977,567	11/02/99	Verdiell			
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	RM	5,621,227	04/15/97	Joshi			
	RN	6,389,209 B1	05/14/02	Suhir			
	RO	5,163,118	11/10/92	Lorenzo et al.			
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BMB	SA	6,156,581	12/05/00	Vaudo et al.			
	SB	5,395,663	03/07/95	Tabata et al.			
	SC	4,146,297	03/27/79	Alfemess et al.			
	SD	5,452,118	09/19/95	Maruska			
	SE	5,889,296	03/30/99	Imamura et al.			
	SF	6,300,615 B1	10/09/01	Shinohara et al.			
	SG	6,232,910 B1	05/15/01	Bell et al.			
	SH	5,686,741	11/11/97	Ohori et al.			
	SI	4,959,702	09/25/90	Moyer et al			
	SJ	6,100,578	08/08/00	Suzuki			
	SK	6,410,947 B1	06/25/02	Wada			
	SL	6,417,059 B2	07/09/02	Huang			
	SM	6,461,927 B1	10/08/02	Mochizuki et al.			
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	SP	5,981,980	11/09/99	Miyajima et al.			
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	TC	5,561,305	10/01/96	Smith			
	TD	5,896,476	04/20/99	Wisseman et al.			
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	TK	5,852,687	12/22/98	Wickham			
	TL	5,122,852	06/16/92	Chan et al.			
	TM	5,173,835	12/22/92	Cornett et al.			
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	TO	6,139,483	10/31/00	Seabaugh et al.			
	TP	5,283,462	02/01/94	Stengel			
	TQ	6,103,403	08/15/00	Grigorian et al.			

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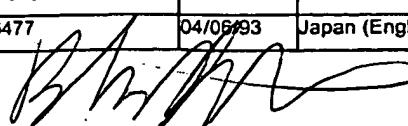
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PNB	UA	5,635,433	06/03/97	Sengupta			
	UB	5,427,988	06/27/95	Sengupta et al.			
	UC	6,297,842 B1	10/02/01	Koizumi et al.			
	UD	5,682,046	10/28/97	Takahashi et al.			
	UE	5,181,085	01/19/93	Moon et al.			
	UF	6,051,858	04/18/00	Uchida et al.			
	UG	6,013,553	01/11/00	Wallace et al.			
	UH	4,872,046	10/03/89	Morkoc et al.			
	UI	2002/0047123 A1	04/25/02	Ramdani et al.			
	UJ	5,995,528	11/30/99	Fukunaga et al.			
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	UL	5,438,584	08/01/95	Paoli et al.			
	UM	4,503,540	03/05/85	Nakashima et al.			
	UN	5,373,166	12/13/94	Buchan et al.			
	UO	6,278,137 B1	08/21/01	Shimoyama et al.			
	UP	5,623,439	04/22/97	Gotoh et al.			
	UQ	4,981,714	01/01/91	Ohno et al.			
	UR	6,194,753 B1	02/27/01	Seon et al.			
	US	6,326,637 B1	12/04/01	Parkin et al.			
	UT						
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	DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO
BWB	AAA 0 250 171	12/23/87	EP	X
	AAB 0 342 937	11/23/89	EP	X
	AAC 0 455 526	06/11/91	EP	X
	AAD 0 602 568	06/22/94	EP	X
	AAE 0 607 435	07/27/94	EP	X
	AAF 1 001 468	05/17/00	EP	X
	AAG 0 514 018	11/19/92	EP	X
	AAH 0 999 600	05/10/00	EP	X
	AAI 1 319 311	06/04/70	Great Britain	X
	AAJ 5-291299	11/05/93	Japan w/English Abstract	X
	AAK 11-238683	08/31/99	Japan	X
	AAL 11-260835	09/24/99	Japan w/English Abstract	X
	AAM HEI 2-391	01/05/90	Japan w/English Abstract	X
	AAN 5-48072	02/26/93	Japan w/English Abstract	X
	AAO 52-88354	07/23/77	Japan w/English Abstract	X
	AAP 54-134554	10/19/79	Japan w/English Abstract	X
	AAQ 55-87424	07/02/80	Japan w/English Abstract	X
	AAR 61-108187	05/26/86	Japan w/English Abstract	X
	AAS 6-232126	08/19/94	Japan	X
	AAT 6-291299	10/18/94	Japan w/English Abstract	X
	AAU 63-34994	02/15/88	Japan w/English Abstract	X
	AAV 63-131104	06/03/88	Japan w/English Abstract	X
	AAW 63-198365	08/17/88	Japan w/English Abstract	X
	AAX 10-321943	12/04/98	Japan	X
	AAY 6-334168	12/02/94	Japan	X
	AAZ WO 99/635580	12/09/99	WIPO	X
	ABA WO 99/14804	03/25/99	WIPO	X
	ABB WO 97/45827	12/04/97	WIPO	
	ABC WO 99/19546	04/22/99	WIPO	
	ABD WO 00/33363	06/08/00	WIPO	
	ABE WO 00/48239	08/17/00	WIPO	
	ABF WO 99/14797	03/25/99	WIPO	
	ABG GB 2 335 792	09/29/99	Great Britain	
	ABH 1 109 212	06/20/01	Europe	
	ABI DE 197 12 496	10/30/97	Germany	X
	ABJ 60-212018	10/24/85	Japan w/English Abstract	
	ABK 60-210018	10/22/85	Japan w/English Abstract	
	ABL WO 92/10875	06/25/92	WIPO	
	ABM 0 682 266	11/15/95	Europe	
	ABN 3-41783	02/91	Japan (English Abstract only)	
	ABO 0 581 239	02/02/94	Europe	
	ABP 0812494	01/16/96	Japan	
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		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO
BAA	1 043 426	10/11/00	Europe		
BAB	2000-068466	03/00	Japan (Abstract)		
BAC	64-50575	02/27/89	Japan		
BAD	WO 98/05807	01/12/98	WIPO		
BAE	WO 94/03908	02/17/94	WIPO		
BAF	WO 01/33585	05/10/01	WIPO		
BAG	1-102435	04/20/89	Japan w/English Abstract		
BAH	52-135684	11/12/77	Japan (English Abstract)		
BAI	02051220	02/21/90	Japan (English Abstract)		
BAJ	11135614	05/21/99	Japan (w/English Abstract)		
BAK	64-52329	02/28/89	Japan (w/English Abstract)		
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BAM	DE 196 07 107	08/28/97	Germany	xx	
BAN	10-303396	11/13/98	Japan (w/English Abstract)		
BAO	58-213412	12/12/83	Japan w/English Abstract		
BAP	0 964 259	12/15/99	Europe		
BAQ	0 875 922	11/04/98	Europe		
BAR	61-63015	04/01/86	Japan w/English Abstract		
BAS	11340542	12/10/99	Japan (English Abstract)		
BAT	WO 01/37330	05/25/01	WIPO		
BAU	0 331 467	09/06/89	Europe		
BAV	WO 00/16378	03/23/00	WIPO		
BAW	0 926 739	06/30/99	Europe		
BAX	0 964 453	12/15/99	Europe		
BAY	5-152529	06/18/93	Japan w/English Abstract		
BAZ	9-67193	03/11/97	Japan w/English Abstract		
BBA	9-82913	03/28/97	Japan w/English Abstract		
BBB	0 309 270	03/29/89	Europe		
BBC	EP 0 957 522	11/17/99	Europe		
BBD	EP 0 810 666	12/03/97	Europe		
BBE	1-179411	07/17/89	Japan w/English Abstract		
BBF	DE 100 17 137	10/26/00	GERMANY		
BBG	WO 02 01648	01/03/02	WIPO		
BBH	WO 02/33385 A2	04/25/02	WIPO		
BBI	WO 01/59814 A2	08/16/01	WIPO		
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BB	CAA 52-89070	07/26/77	Japan	xx
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	CAD WO 02/03467	01/10/02	WIPO	
	CAE 0 630 057	12/21/94	EUROPE	
	CAF 61-36981	02/21/86	Japan w/English Abstract	
	CAG WO 93/07647	04/15/93	WIPO	
	CAH 2002-9366	01/11/02	Japan w/English Abstract	
	CAI EP 0 881 669	12/02/98	Europe	
	CAJ WO 02/03480	01/10/02	WIPO	
	CAK WO 02/50879	06/27/02	WIPO	
	CAL EP 0 777 379	06/04/97	Europe	
	CAM WO 01/04943 A1	01/18/01	WIPO	xx
	CAN WO 02/47127 A2	06/13/02	WIPO	
	CAO JP 58-075868	05/07/83	Japan w/English Abstract	
	CAP EP 0 993 027	04/12/00	Europe	
	CAQ EP 0 711 853	05/15/96	Europe	
	CAR WO 98/20606	05/14/98	WIPO	
	CAS EP 1 043 765	10/11/00	Europe	
	CAT 0 300 499	01/25/89	Europe	
	CAU EP 1 085 319	03/21/01	Europe	
	CAV WO 01/16395	03/08/01	WIPO	
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b/wb	CCAA	Nakagawara et al., "Effects of Buffer Layers in Epitaxial Growth of SrTiO ₃ Thin Film on Si(100), <i>J. Appl. Phys.</i> , 78 (12), December 15, 1995, pp. 7226-7230.			
	CCAB	Suzuki et al., "A Proposal of Epitaxial Oxide Thin Film Structures For Future Oxide Electronics," <i>Materials Science and Engineering B</i> 41, (1996), pp. 166-173.			
	CCAC	W. F. Egelhoff et al., "Optimizing GMR Spin Valves: The Outlook for Improved Properties", <i>1998 Int'l Non Volatile Memory Technology Conference</i> , pp. 34-37.			
	CCAD	Wang et al., "Processing and Performance of Piezoelectric Films", Univ. Of MD, Wilcoxon Research Col, and Motorola Labs, May 11, 2000.			
	CCAE	M. Rotter et al., "Nonlinear Acoustoelectric Interactions in GaAs/LiNbO ₃ Structures", <i>Applied Physics Letters</i> , Vol. 75(7), August 16, 1999, pp. 965-967.			
	CCAF	K. Sreenivas et al., "Surface Acoustic Wave Propagation on Lead Zirconate Titanate Thin Films," <i>Appl. Phys. Lett.</i> 52 (9), Feb. 29, 1988, pp. 709-711.			
	CCAG	M. Rotter et al., "Single Chip Fused Hybrids for Acousto-Electric and Acousto-Optic Applications," <i>1997 Applied Physics Letters</i> , Vol. 70(16), April 21, 1997, pp. 2097-2099.			
	CCAH	A. Mansingh et al., "Surface Acoustic Wave Propagation in PZT/YBCO/SrTiO ₃ and PbTiO ₃ /YBCO/SrTiO ₃ Epitaxial Heterostructures," <i>Ferroelectric</i> , Vol. 224, pages 275-282, 1999.			
	CCAI	S. Mathews et al., "Ferroelectric Field Effect Transistor Based on Epitaxial Perovskite Heterostructures", <i>Science</i> , Vol. 276, April 11, 1997, pp. 238-240.			
	CCAJ	R. Houdre et al., "Properties of GaAs on Si Grown by Molecular Beam Epitaxy," <i>Solid State and Materials Sciences</i> , Vol. 16, Issue 2, 1990, pp. 91-114.			
	CCAK	S. F. Fang et al., "Gallium Arsenide and Other Compound Semiconductors on Silicon," <i>J. Appl. Phys.</i> , 68(7), October 1, 1990, pp. R31-R58.			
	CCAL	Carlin et al., "Impact of GaAs Buffer Thickness on Electronic Quality of GaAs Grown on Graded Ge/GeSi/Si Substrates, <i>Appl. Phys. Letter</i> , Vol. 76, No. 14, April 2000, pp. 1884-1886.			
	CCAM	Ringel et al., "Epitaxial Integration of III-V Materials and Devices with Si Using Graded GeSi Buffers," <i>27th International Symposium on Compound Semiconductors</i> , Oct. 2000.			
	CCAN	Zogg et al., "Progress in Compound-Semiconductor-on-Silicon-Heteroepitaxy with Fluoride Buffer Layers," <i>J. Electrochem Soc.</i> , Vol. 136, No. 3, March 1998, pp. 775-779.			
	CCAO	Xiong et al., "Oxide Defined GaAs Vertical-Cavity Surface-Emitting Lasers on Si Substrates," <i>IEEE Photonics Technology Letters</i> , Vol. 12, No. 2, Feb. 2000, pp. 110-112.			
	CCAP	Clem et al., "Investigation of PZT//LSCO//Pt//Aerogel Thin Film Composites for Uncooled Pyroelectric IR Detectors," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 541, pp. 661-666, 1999.			
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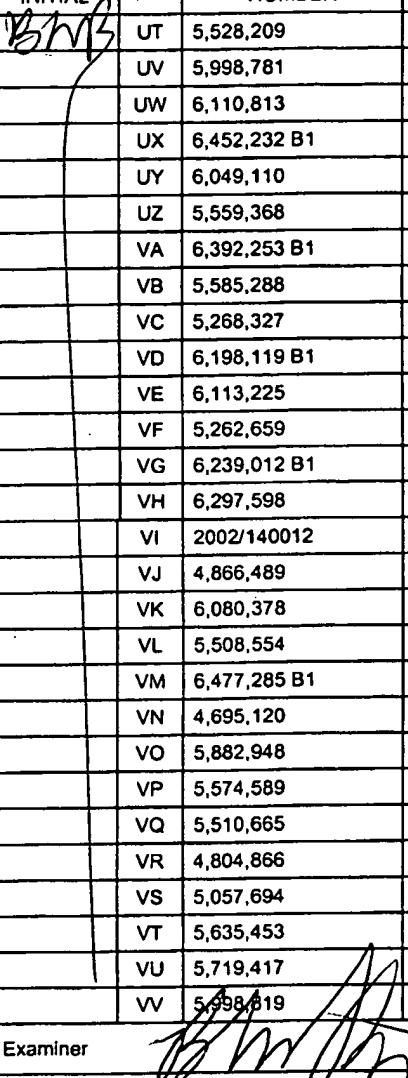
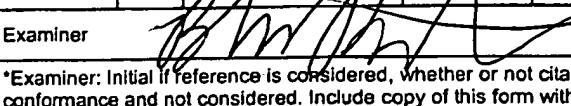
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	JJAN	P.J. Borrelli et al.; "Compositional and Structural Properties of Sputtered PLZT Thin Films"; Ferroelectric Thin Films II Symposium; Dec. 2-4, 1991 (Abstract)	
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LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Jamal RAMDANI, et al.		
		FILING DATE February 2, 2004	GROUP 2815	
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)				
6W3	KKAA	V. Kaushik et al.; "Device Characteristics of Crystalline Epitaxial Oxides on Silicon"; Device Research Conference, 2000; Conference Digest 58th DRC; pp. 17-20; June 19-21, 2000		
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	KKAC	Alex Chediak et al; "Integration of GaAs/Si with Buffer Layers and Its Impact on Device Integration"; TICS 4, Prof. Sands. MSE 225, April 12, 2002; pp. 1-5		
	KKAD	S.A. Chambers et al; "Band Discontinuities at Epitaxial SrTiO ₃ /Si(001) Heterojunctions"; Applied Physics Letters; Vol. 77, No. 11; September 11, 2000; pp. 1662-1664		
	KKAE	H. Wang et al.; "GaAs/GaAlAs Power HBTs for Mobile Communications"; Microwave Symposium Digest; 1993 IEEE; Vol. 2.; pp. 549-552		
	KKAF	Y. Ota et al.; "Application of Heterojunction FET to Power Amplifier for Cellular Telephone"; Electronics Letters; 26th May 1994; Vol. 30, No. 11; pp. 906-907		
	KKAG	Keiichi Sakuno et al; "A 3.5W HBT MMIC Power Amplifier Module for Mobile Communications"; IEEE 1994; Microwave and Millimeter-Wave Monolithic Circuits Symposium; pp. 63-66		
	KKAH	Mitsubishi Semiconductors Press Release (GaAs FET's) November 8, 1999 pp.1-2		
	KKAI	R.J. Matyi et al; "Selected Area Heteroepitaxial Growth of GaAs on Silicon for Advanced Device Structures"; 2194 Thin Solid Films; 181 (1989) December 10; No. 1; pp. 213-225		
	KKAJ	K. Nashimoto et al; "Patterning of Nb, LaOnZr, TiO ₃ Waveguides for Fabricating Micro-Optics Using Wet Etching and Solid-Phase Epitaxy"; Applied Physics Letters; Vol. 75, No. 8; 23 August 1999; pp. 1054-1056		
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	KKAO			
	KKAP			
	KKAQ			
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SHEET 1 OF 5

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U.S. PATENT DOCUMENTS								
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	UT	5,528,209	06/18/96	Macdonald et al.				
	UV	5,998,781	12/07/99	Vawter et al.				
	UW	6,110,813	08/29/00	Ota et al.				
	UX	6,452,232 B1	09/17/02	Adan				
	UY	6,049,110	04/11/00	Koh				
	UZ	5,559,368	09/24/96	Hu et al.				
	VA	6,392,253 B1	05/21/02	Saxena				
	VB	5,585,288	12/17/96	Davis et al.				
	VC	5,268,327	12/07/93	Vernon				
	VD	6,198,119 B1	03/06/01	Nabatame et al.				
	VE	6,113,225	09/05/00	Miyata et al.				
	VF	5,262,659	11/16/93	Grudkowski et al.				
	VG	6,239,012 B1	05/29/01	Kinsman				
	VH	6,297,598	10/02/01	Wang et al.				
	VI	2002/140012	10/03/02	Droopad				
	VJ	4,866,489	09/12/89	Yokogawa et al.				
	VK	6,080,378	06/27/00	Yokota et al.				
	VL	5,508,554	04/16/96	Takatani et al.				
	VM	6,477,285 B1	11/05/02	Shanley				
	VN	4,695,120	09/22/87	Holder				
	VO	5,882,948	03/16/99	Jewell				
	VP	5,574,589	11/12/96	Feuer et al.				
	VQ	5,510,665	04/23/96	Conley				
	VR	4,804,866	02/14/89	Akiyama				
	VS	5,057,694	10/15/91	Idaka et al.				
	VT	5,635,453	06/03/97	Pique et al.				
	VU	5,719,417	02/17/98	Roeder et al.				
	VV	5,998,619	12/07/99	Yokoyama et al.				
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	VW	2002/0079576	06/27/02	Seshan			
	VX	5,148,504	09/15/92	Levi et al.			
	VY	2002/0195610 A1	12/26/02	Klosowiak			
	VZ	5,477,363	12/19/95	Matsuda			
	WA	5,905,571	05/18/99	Butler et al.			
	WB	5,570,226	10/29/96	Ota			
	WC	5,087,829	02/11/92	Ishibashi et al.			
	WD	2001/0020278 A1	09/06/01	Saito			
	WE	6,496,469 B1	12/17/02	Uchizaki			
	WF	5,679,947	10/21/97	Doi et al.			
	WG	2001/0036142 A1	11/01/01	Kadowaki et al.			
	WH	5,446,719	08/29/95	Yoshida et al.			
	WI	5,831,960	11/03/98	Jiang et al.			
	WJ	5,693,140	12/02/97	McKee et al.			
	WK	6,376,337 B1	04/23/02	Wang et al.			
	WL	4,177,094	12/04/79	Kroon			
	WM	5,216,359	06/01/93	Makki et al.			
	WN	6,307,996 B1	10/23/01	Nashimoto et al.			
	WO	5,371,621	12/06/94	Stevens			
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	WQ	3,617,951	11/02/71	Anderson			
	WR	5,838,053	11/17/98	Bevan et al.			
	WS	5,684,302	11/04/97	Wersing et al.			
	WT	5,959,308	09/28/99	Shichijo et al.			
	WU	5,362,972	11/08/94	Yazawa et al.			
	WV	5,864,171	01/26/99	Yamamoto et al.			
	WW	5,028,563	07/02/91	Feit et al.			
	WX	5,937,145	08/10/99	Domash			
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<i>BBW3</i>	WY	5,878,175	03/02/99	Sonoda et al.			
	WZ	4,801,184	01/31/89	Revelli			
	XA	5,140,387	08/18/92	Okazaki et al.			
	XB	5,410,622	04/25/95	Okada et al.			
	XC	6,064,783	05/16/00	Congdon et al.			
	XD	5,772,758	06/30/98	Collins et al.			
	XE	5,666,376	09/09/97	Cheng			
	XF	5,976,953	11/02/99	Zavracky et al.			
	XG	5,578,162	11/26/96	D'Asaro et al.			
	XH	5,585,167	12/17/96	Satoh et al.			
	XI	5,674,813	10/07/97	Nakamura et al.			
	XJ	5,574,296	11/12/96	Park et al.			
	XK	6,504,189	01/07/03	Matsuda et al.			
	XL	5,987,196	11/16/99	Noble			
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	XN						
	XO						
	XP						
	XQ						
	XR						
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	XZ						
Examiner <i>BBW3</i>				Date Considered <i>1/2/05</i>			

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CBM	CBC	EP 1 035 759	09/13/00	Europe	
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	CBF	5-243525	09/31/93	JAPAN W/ENGLISH ABSTRACT	
	CBG	3-171617	07/25/91	JAPAN W/ENGLISH ABSTRACT	
	CBH	EP 1 089 338	04/04/01	EUROPE	
	CBI	01 294594	11/28/99	JAPAN (ABSTRACT)	
	CBJ	05 221800	08/31/93	JAPAN (ABSTRACT)	
	CBK	03-149882	11/07/89	JAPAN	
	CBL	0 614 256	09/07/94	EUROPE	
	CBM	1 054 442	11/22/00	EUROPE	
	CBN	0 852 416	07/08/98	EUROPE	
	CBO	WO 02/08806	01/31/02	WIPO	
	CBP	WO 01/59837	08/16/01	WIPO	
	CBQ	62-245205	10/26/87	JAPAN W/ENGLISH ABSTRACT	
	CBR	0 600 658	06/08/94	EUROPE	
	CBS	0 412 002	02/06/91	EUROPE	
	CBT	2000-349278	12/15/00	JAPAN (ENGLISH ABSTRACT)	
	CBU	01-196809	08/08/89	JAPAN (ENGLISH ABSTRACT)	
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		OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)		
BM	KKAO	Charles Kittel: "Introduction to Solid State Physics"; John Wiley & Sons, Inc. Fifth Edition; pp. 415		
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	KKAS	Yoshihiro Yokota et al.: "Cathodoluminescence of boron-doped heteroepitaxial diamond films on platinum"; Diamond and Related Materials 8(1999); pp. 1587-1591		
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	KKAW	Lin Li: "Ferroelectric/Superconductor Heterostructures"; Materials Science and Engineering; 29 (2000) pp. 153-181		
	KKAX	L. Fan et al.: "Dynamic Beam Switching of Vertical-Cavity Surface-Emitting Lasers with Integrated Optical Beam Routers"; IEEE Photonics Technology Letters; Vol. 9, No. 4; April 4, 1997; pp. 505-507		
	KKAY	Y. Q. Xu. et al.: "(Mn, Sb) doped-Pb(Zr,Ti)O ₃ infrared detector arrays"; Journal of Applied Physics; Vol. 88, No. 2; 15 July 2000; pp. 1004-1007		
	KKAZ	Kiyoko Kato et al.: "Reduction of dislocations in InGaAs layer on GaAs using epitaxial lateral overgrowth"; 2300 Journal of Crystal Growth 115 (1991) pp. 174-179; December 1991		
	LLAA			
	LLAB			
	LLAC			
	LLAD			
	LLAE			
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SHEET 1 OF 4

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	XN	6,233,435 B1	05/15/01	WONG			
	XO	4,723,321	02/02/88	SALEH			
	XP	6,181,920 B1	01/30/01	DENT ET AL			
	XQ	6,415,140 B1	07/02/02	BENJAMIN ET AL			
	XR	5,760,740	06/02/98	BLODGETT			
	XS	5,238,877	08/24/93	RUSSELL			
	XT	4,876,218	10/24/89	PESSA ET AL			
	XU	6,232,242 B1	05/15/01	HATA ET AL			
	XV	4,378,259	03/29/83	HASEGAWA ET AL			
	XW	6,278,541 B1	08/21/01	BAKER			
	XY	4,298,247	11/03/81	MICHELET ET AL			
	XZ	4,174,504	11/13/79	CHENAUSKY ET AL			
	YA	3,758,199	09/11/73	THAXTER			
	YB	6,362,558 B1	03/26/02	FUKUI			
	YC	6,140,746	10/31/00	MIYASHITA ET AL			
	YD	2002/0076878 A1	06/20/02	WASA ET AL			
	YE	6,419,849 B1	07/16/02	QIU ET AL			
	YF	2002/0179000 A1	12/05/02	LEE ET AL			
	YG	6,341,851	01/29/02	TAKAYAMA ET AL			
	YH	2001/0055820 A1	12/27/01	SAKURAI ET AL			
	YI	6,204,525 B1	03/20/01	SAKURAI ET AL			
	YJ	5,985,404	11/16/99	YANO ET AL			
	YK	6,538,359 B1	03/25/03	HIRAKU ET AL			
	YL	6,498,358 B1	12/24/02	LACH ET AL			
	YM	5,387,811	02/07/95	SAIGOH			
	YN	5,523,602	06/04/96	HORIUCHI ET AL			
	YO	5,362,998	11/08/94	IWAMURA ET AL			
	YP	5,188,976	02/23/93	KUME ET AL			
Examiner	<i>B. Smith</i>				Date Considered		<i>1/2/05</i>

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	YS	5,238,877	08/24/93	RUSSELL			
	YT	5,540,785	07/30/96	DENNARD ET AL			
	YU	5,997,638	12/07/99	COPEL ET AL			
	YV	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL			
	YY	2002/0021855	02/21/02	KIM			
	YZ	6,110,840	08/29/00	YU			
	ZA	5,667,586	09/16/97	EK ET AL			
	ZB	5,313,058	05/17/94	FRIEDERICH ET AL			
	ZC	5,315,128	05/24/94	HUNT ET AL			
	ZD	5,919,522	07/06/99	BAUM ET AL			
	ZE	4,843,609	06/27/89	OHYA ET AL			
	ZF	4,626,878	12/02/86	KUWANO ET AL			
	ZG	4,525,871	06/25/85	FOYT ET AL			
	ZH	3,818,451	06/18/74	COLEMAN			
	ZI	6,059,895	05/09/00	CHU ET AL			
	ZJ	4,447,116	05/08/84	KING ET AL			
	ZK	6,022,671	02/08/00	BINKLEY ET AL			
	ZL	5,754,714	05/19/98	SUZUKI ET AL			
	ZM	6,524,651 B2	02/25/03	GAN ET AL			
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL			
	ZO	5,642,371	06/24/97	TOHYAMA ET AL			
	ZP	6,445,724 B2	09/03/02	ABELES			
	ZQ	5,753,934	05/19/98	YANO ET AL			
	ZR	6,326,667 B1	12/04/01	SUGIYAMA ET AL			
	ZS	6,051,874	04/18/00	MASUDA			
	ZT	5,166,761	11/24/92	OLSON ET AL			
	ZU	5,514,744	11/12/96	GAW ET AL			
Examiner <i>BWJ</i>					Date Considered <i>1/2/05</i>		

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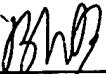
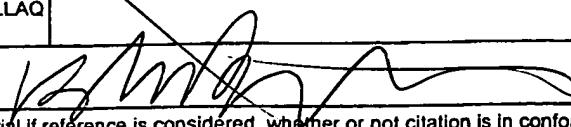
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		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	TRANSLATION NO
BNP	CCA	5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT		
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	CCC	2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT		
	CCD	2000-278085	10/06/00	JAPAN (ENGLISH ABSTRACT)		
	CCE	WO 03/012874	02/13/03	WIPO		
	CCF	1 043 427	10/11/00	EUROPE		
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	CCI	10-269842	10/09/98	JAPAN W/ENGLISH ABSTRACT		
	CCJ	59066183	04/14/84	JAPAN (ENGLISH ABSTRACT)		
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	CCS	0 392 714	10/17/90	EUROPE		
	CCT					
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LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Jamal RAMDANI, et al.		
		FILING DATE February 2, 2004	GROUP 2815	
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)				
	LLAA	Peter Weiss; "Speed demon gets hooked on silicon"; Science News Online; Sept. 15, 2001; pp. 1-3		
	LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001		
	LLAC	Lori Valigra; "Motorola Lays GaAs on Si Wafer"; AsiaBizTech; Nov. 2001 pp. 1-3		
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Examiner			Date Considered 1/2/05	
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.				

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LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Jamal RAMDANI, et al.					
		FILING DATE February 2, 2004		GROUP 2815			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>PM</i>	ZV	5,122,679	06/16/92	ISHII ET AL			
	ZW	6,232,806	05/15/01	WOESTE ET AL			
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	A9						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION <i>Chas G.W. O'Neil</i>		
	CCS	WO 99/67882	12/29/99	WIPO	YES	NO	
	CCT	WO 95/02904	01/26/95	WIPO			
	CCU	WO 02/009150	01/31/02	WIPO			
	CCV	0 766 292	04/02/97	EUROPE			
	CCW	198 29 609	01/05/00	GERMANY			
	CCX	1 069 605	01/17/01	EUROPE			
	CCY	0 828 287	03/11/98	EUROPE			
	CCZ	1 176 230	01/30/02	EUROPE			
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	LLAP	YI W. et al; "Mechanism of cleaning Si (100) surface using Sr and SrO for the growth of crystalline SrTiO/sub 2/films" Journal of Vacuum Science & Technology, Vol. 20, No. 4, July 2002 (2002-07) pp. 1402-1405					
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	LLAS				<input type="checkbox"/> Additional References sheet(s) attached		
Examiner				Date Considered 1/2/05			
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